

4/2000
4/2001

IN THE CLAIMS:

Claims 1-30. (Cancelled).

31. (Currently Amended) A method of manufacturing ~~method of~~ a semiconductor device including ~~a CMOS circuit formed by~~ an n-channel TFT and a p-channel TFT comprising the steps of:

~~a process of~~ forming a first wiring line on a substrate,
~~a process of~~ forming a first insulating layer on the first wiring line,
~~a process of~~ forming an active layer of the n-channel TFT and an active layer of the p-channel TFT on the first insulating layer, wherein the active layer of the n-channel TFT is located over the first wiring line with the first insulating film interposed therebetween and the active layer of the p-channel TFT does not overlap any portion of the first wiring line,
~~a process of~~ forming a second insulating layer by overlapping on the active layer of the n-channel TFT and the active layer of the p-channel layer TFT, and
~~a process of~~ forming a second wiring line on the second insulating layer, and
~~a process of~~ forming a LDD region on in the active layer of the n-channel TFT; and
wherein the LDD region is provided overlap overlapping the first wiring line and not to overlap overlapping the second wiring line.

32. (Currently Amended) ~~Manufacturing~~ The method of manufacturing a the semiconductor device according to claim 31, ~~characterized in that~~

wherein each of the first wiring line and ~~the~~ second wiring line is ~~formed by~~ made of a conductive film ~~mainly~~ containing an element selected from the group consisting of tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si), ~~or an alloy film or silicide film containing the above elements in combination.~~

33. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a first conductive film over a substrate;

patterning ~~said~~ the first conductive film to form at least one first wiring line, ~~said first wiring including at least one first gate electrode~~;

forming a first insulating film over ~~said~~ the first wiring line and ~~said~~ the substrate;

forming a first semiconductor island and a second semiconductor island, wherein ~~said~~ the first semiconductor island is located over said the first ~~gate electrode wiring line~~ with ~~said~~ the first insulating film interposed therebetween and ~~said~~ the second semiconductor island does not overlap any portion of the first conductive film;

forming a pair of first N-type impurity regions in the first semiconductor island with a first channel region therebetween;

forming at least one second N-type impurity region between the first channel region and the first N-type impurity regions, wherein a concentration of an N-type impurity in the second N-type impurity region is lower than that in ~~said~~ the first N-type impurity regions;

forming a pair of P-type impurity regions in the second semiconductor island with a second channel region therebetween;

forming a second insulating film over said the first semiconductor island and the second semiconductor ~~islands~~ island; and

forming a second ~~gate electrode wiring line~~ over the first channel region of the first semiconductor island and a third ~~gate electrode wiring line~~ over the second channel region of the second semiconductor island,

wherein there is an overlap between the first ~~gate electrode wiring line~~ and the second N-type impurity region of the first semiconductor island and there is no overlap between the second ~~gate electrode wiring line~~ and the second N-type impurity region.

34. (Currently Amended) The method of manufacturing the semiconductor device according to claim 33,

wherein ~~said~~ the first conductive film comprises a material selected from the group consisting of Ta, Cr, Ti, W, Mo ~~and~~ is tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

35. (Currently Amended) The method of manufacturing the semiconductor device according to claim 33,

wherein ~~said~~ the second wiring line and the third gate-electrodes wiring line are formed by patterning a second conductive layer film, ~~said the second~~ conductive layer film comprising a material selected from the group consisting of tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

36. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a first conductive film over a substrate;

patterning ~~said the first~~ conductive film to form at least one first wiring line, ~~said first wiring including at least one first gate-electrode~~;

forming a first insulating film over ~~said the first wiring line~~ and ~~said the~~ substrate;

forming a first semiconductor island and a second semiconductor island, wherein ~~said the first semiconductor island is located over said the first gate-electrode wiring line with said the first insulating film interposed therebetween and said the second semiconductor island does not overlap any portion of the first~~ conductive film;

forming a pair of first N-type impurity regions in the first semiconductor island with a first channel region therebetween;

forming at least one second N-type impurity region between the first channel region and the first N-type impurity regions, wherein a concentration of an N-type impurity in the second N-type impurity region is lower than that in ~~said the first N-type impurity regions~~;

forming a pair of P-type impurity regions in the second semiconductor island with a second channel region therebetween;

forming a second insulating film over ~~said the first semiconductor island and the second semiconductor islands island; and~~

forming a second ~~gate-electrode wiring line~~ wiring line over the first channel region of the first semiconductor island and a third ~~gate-electrode wiring line~~ wiring line over the second channel region of the second semiconductor island,

wherein there is an overlap between the first ~~gate-electrode wiring line~~ wiring line and the second N-type impurity region of the first semiconductor island and there is no overlap between the second ~~gate-electrode wiring line~~ wiring line and the second N-type impurity region, and

wherein the first ~~gate-electrode~~ wiring line is electrically connected to the second ~~gate electrode~~ wiring line.

37. (Currently Amended) The method of manufacturing the semiconductor device according to claim 36,

wherein ~~said the first~~ the first conductive film comprises a material selected from the group consisting of ~~Ta, Cr, Ti, W, Mo and Si~~ tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

38. (Currently Amended) The method of manufacturing the semiconductor device according to claim 36,

wherein ~~said the~~ the second wiring line and ~~the third gate-electrodes~~ the third wiring line are formed by patterning a second conductive ~~layer film~~ layer film, ~~said the second~~ the second conductive ~~layer film~~ layer film comprising a material selected from the group consisting of tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

39. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a first conductive film over a substrate;

patterning ~~said the first~~ the first conductive film to form at least one first wiring line, ~~said first wiring including at least one first gate electrode~~;

forming a first insulating film over ~~said the~~ the first wiring line and ~~said the~~ the substrate;

forming a first semiconductor island and a second semiconductor island, wherein ~~said the~~ the first semiconductor island is located over ~~said the~~ the first ~~gate-electrode~~ wiring line with ~~said the~~ the first insulating film interposed therebetween and ~~said the~~ the second semiconductor island does not overlap any portion of the first conductive film;

forming a pair of first N-type impurity regions in the first semiconductor island with a first channel region therebetween;

forming at least one second N-type impurity region between the first channel region and the first N-type impurity regions, wherein a concentration of an N-type impurity in the second N-type impurity region is lower than that in ~~said the~~ the first N-type impurity regions;

forming a pair of P-type impurity regions in the second semiconductor island with a second channel region therebetween;

forming a second insulating film over said the first semiconductor island and the second semiconductor islands island; and

forming a second ~~gate-electrode~~ wiring line over the first channel region of the first semiconductor island and a third ~~gate-electrode~~ wiring line over the second channel region of the second semiconductor island,

wherein the first ~~gate-electrode~~ wiring line extends beyond both side edges of the second ~~gate-electrode~~ wiring line.

40. (Currently Amended) The method of manufacturing the semiconductor device according to claim 39,

wherein ~~said the first~~ conductive film comprises a material selected from the group consisting of ~~Ta, Cr, Ti, W, Mo and Si~~ tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

41. (Currently Amended) The method of manufacturing the semiconductor device according to claim 39,

wherein ~~said the~~ second wiring line and the third gate-electrodes wiring line are formed by patterning a second conductive layer, ~~said the second~~ conductive layer comprising a material selected from the group consisting of tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

42. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a first conductive film over a substrate;

patterning ~~said the first~~ conductive film to form at least one first wiring line, ~~said first wiring including at least one first gate-electrode~~;

forming a first insulating film over ~~said the~~ first wiring line and ~~said the~~ substrate;

forming a first semiconductor island and a second semiconductor island, wherein ~~said the~~ first semiconductor island is located over ~~said the~~ first gate-electrode wiring line with ~~said~~

the first insulating film interposed therebetween and ~~said~~ the second semiconductor island does not overlap any portion of the first conductive film;

forming a pair of first N-type impurity regions in the first semiconductor island with a first channel region therebetween;

forming at least one second N-type impurity region between the first channel region and the first N-type impurity regions, wherein a concentration of an N-type impurity in the second N-type impurity region is lower than that in ~~said~~ the first N-type impurity regions;

forming a pair of P-type impurity regions in the second semiconductor island with a second channel region therebetween;

forming a second insulating film over ~~said~~ the first semiconductor island and the second semiconductor ~~islands~~ island;

forming a second ~~gate-electrode~~ wiring line over the first channel region of the first semiconductor island and a third ~~gate-electrode~~ wiring line over the second channel region of the second semiconductor island;

forming a third insulating film over the second wiring line and the third ~~gate electrodes~~ wiring line; and

forming a pixel electrode over the third insulating film,

wherein the first ~~gate-electrode~~ wiring line is electrically floating, and

wherein the first ~~gate-electrode~~ wiring line extends beyond both side edges of the second ~~gate-electrode~~ wiring line.

43. (Currently Amended) The method of manufacturing the semiconductor device according to claim 42,

wherein ~~said~~ the first conductive film comprises a material selected from the group consisting of Ta, Cr, Ti, W, ~~Mo and Si~~ tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

44. (Currently Amended) The method of manufacturing the semiconductor device according to claim 42,

wherein ~~said~~ the second wiring line and the third gate-electrodes wiring line are formed by patterning a second conductive layer, ~~said~~ the second conductive layer comprising

a material selected from the group consisting of tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

45. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a first conductive film over a substrate;

patterning ~~said the first~~ conductive film to form at least one first wiring line, ~~said first wiring including at least one first gate electrode~~;

forming a first insulating film over ~~said the first wiring line~~ and ~~said the~~ substrate;

forming a first semiconductor island and a second semiconductor island, wherein ~~said the first semiconductor island is located over said the first gate electrode wiring line with said the first insulating film interposed therebetween and said the second semiconductor island does not overlap any portion of the first~~ conductive film;

forming a pair of first N-type impurity regions in the first semiconductor island with a first channel region therebetween;

forming at least one second N-type impurity region between the first channel region and the first N-type impurity regions, wherein a concentration of an N-type impurity in the second N-type impurity region is lower than that in ~~said the~~ first N-type impurity regions;

forming a pair of P-type impurity regions in the second semiconductor island with a second channel region therebetween;

forming a second insulating film over ~~said the first semiconductor island and the second semiconductor islands island~~; and

forming a second ~~gate electrode wiring line~~ over the first channel region of the first semiconductor island and a third ~~gate electrode wiring line~~ over the second channel region of the second semiconductor island,

wherein the first ~~gate electrode wiring line~~ extends beyond both side edges of the second ~~gate electrode wiring line~~ and is connected to a fixed potential.

46. (Currently Amended) The method of manufacturing the semiconductor device according to claim 45,

wherein ~~said~~ the first conductive film comprises a material selected from the group consisting of ~~Ta, Cr, Ti, W, Mo and Is~~ tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

47. (Currently Amended) The method of manufacturing the semiconductor device according to claim 45,

wherein ~~said~~ the second wiring line and the third gate-electrodes wiring line are formed by patterning a second conductive layer, ~~said the second~~ conductive layer comprising a material selected from the group consisting of tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

48. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a first conductive film over a substrate;

patterning ~~said~~ the first conductive film to form at least one first wiring line, ~~said first wiring including at least one first gate electrode;~~

forming a first insulating film over ~~said~~ the first wiring line and ~~said~~ the substrate;

forming a first semiconductor island and a second semiconductor island, wherein ~~said~~ the first semiconductor island is located over ~~said~~ the first gate-electrode wiring line with ~~said~~ the first insulating film interposed therebetween and ~~said~~ the second semiconductor island does not overlap any portion of the first conductive film;

forming a second insulating film over ~~said~~ the first semiconductor island and the second semiconductor islands island;

forming a second conductive film over the second insulating film;

first etching a portion of the second conductive film to form a second gate-electrode wiring line over the first semiconductor island while a portion of the conductive film over the second semiconductor island is not etched, wherein ~~said~~ the first gate-electrode wiring line extends beyond side edges of the ~~second-gate-electrode~~ first semiconductor island;

first introducing an N-type impurity into the first semiconductor island at a first concentration in accordance with a pattern of the second gate-electrode wiring line, wherein

~~said the~~ N-type impurity ~~region~~ is prevented from being introduced into the second semiconductor island during the first ~~introduction of~~ introducing the N-type impurity;

second etching another portion of the second conductive film to form a third gate electrode wiring line over the second semiconductor island after the ~~introduction of~~ first introducing of the N-type impurity;

introducing a P-type impurity into the second semiconductor island in accordance with a pattern of the third ~~gate electrode wiring line~~, wherein ~~said the~~ P-type impurity is prevented from being introduced into the first semiconductor island during the ~~introduction of~~ said introducing the P-type impurity;

forming a first resist mask and a second resist mask, wherein ~~said the~~ first resist mask covers the second ~~gate electrode wiring line~~ and extends beyond side edges of the second ~~gate electrode wiring line~~, and ~~said the~~ second resist mask is formed over the third ~~gate electrode wiring line~~;

second introducing an N-type impurity into the first semiconductor island in accordance with ~~said the~~ first resist mask and the second resist mask at a second concentration greater than the first concentration.

49. (Currently Amended) The method of manufacturing the semiconductor device according to claim ~~39~~ 48,

wherein ~~said the first~~ conductive film comprises a material selected from the group consisting of ~~Ta, Cr, Ti, W, Mo and Si~~ tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

50. (Currently Amended) The method of manufacturing the semiconductor device according to claim ~~39~~ 48,

wherein ~~said the second and third gate electrodes are formed by patterning a~~ conductive layer, ~~said~~ conductive layer comprising a material selected from the group consisting of tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).